SKiiP 37NAB066V1



MiniSKiiP[®] 3

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter SKiiP 37NAB066V1

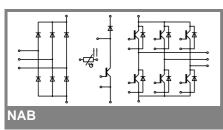
Target Data

Features

- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

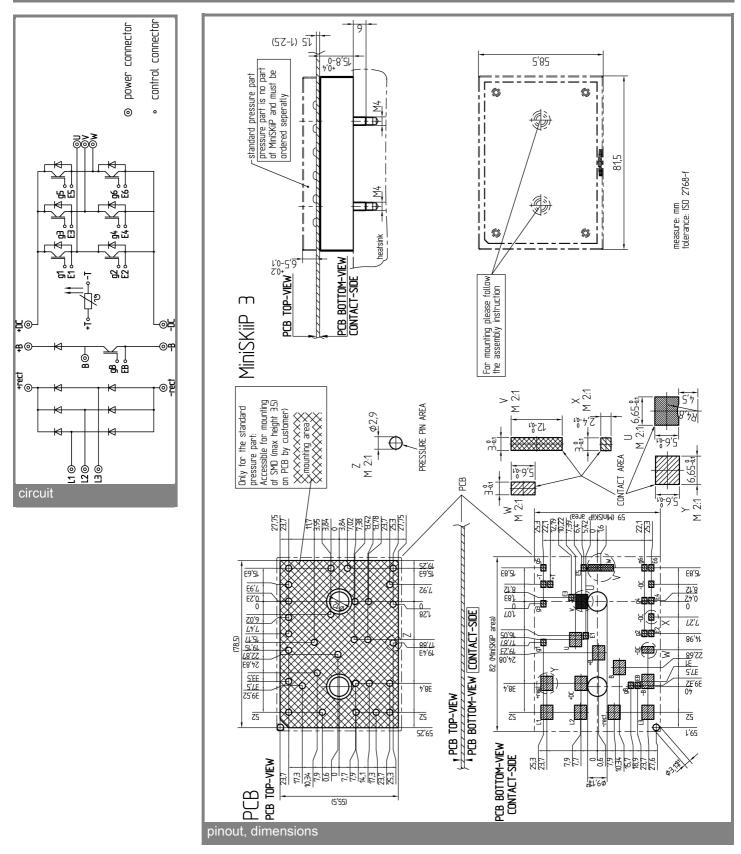
- Inverter up to 18 kVA
- Typical motor power 7,5 kW



Absolute	Maximum Ratings	$T_s = 25 \text{ °C}$, unless otherwise specified					
Symbol	Conditions	Values	Units				
IGBT - Inverter, Chopper							
V _{CES}		600	V				
Ι _C	T _s = 25 (70) °C		А				
ICRM	$T_s = 25 (70) \ ^{\circ}C, t_p \le 1 \ ms$		A				
V _{GES}		± 20	V				
Т _ј		- 40 + 150	°C				
Diode - Inverter, Chopper							
I _F	T _s = 25 (70) °C		А				
I _{FRM}	$T_s = 25 (70) \ ^{\circ}C, t_p \le 1 \ ms$		А				
Т _ј		- 40 + 150	°C				
Diode - Rectifier							
V _{RRM}		800	V				
I _F	T _s = 70 °C	61	А				
I _{FSM}	t _p = 10 ms, sin 180 °, T _j = 25 °C	700	А				
i²t	t _p = 10 ms, sin 180 °, T _j = 25 °C	2400	A²s				
Т _ј		- 40 + 150	°C				
I _{tRMS}	per power terminal (20 A / spring)	80	А				
T _{stg}	$T_{op} \leq T_{stg}$	- 40 + 125	°C				
V _{isol}	AC, 1 min.	2500	V				

Characte	ristics	T _s = 25 °C	$T_s = 25$ °C, unless otherwise specified						
Symbol	Conditions	min.	typ.	max.	Units				
IGBT - Inverter, Chopper									
V _{CEsat}	I _C = 60 A, T _j = 25 (125) °C		2 (2,2)	2,5 (2,7)	V				
V _{GE(th)}	$V_{GE} = V_{CE}$, $I_{C} = 1 \text{ mA}$	3	4	5	V				
V _{CE(TO)}	T _j = 25 (125) °C		1,2 (1,1)	1,3 (1,2)	V				
r _T	T _j = 25 (125) °C		13 (18)	20 (25)	mΩ				
Cies	$V_{CE} = 25 \text{ V}, \text{ V}_{GE} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$		3,3		nF				
C _{oes}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,7		nF				
C _{res}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		0,8		nF				
R _{th(j-s)}	per IGBT		0,65		K/W				
t _{d(on)}	under following conditions		35		ns				
t _r `´	V _{CC} = 300 V, V _{GE} = ± 15 V		35		ns				
t _{d(off)}	I _C = 60 A, T _i = 125 °C		310		ns				
t _r	$R_{Gon} = R_{Goff} = 20 \Omega$		20		ns				
E _{on}	inductive load		1,8		mJ				
E _{off}			1,4		mJ				
Diode - In	verter, Chopper								
$V_{F} = V_{EC}$	I _F = 60 A, T _i = 25 (125) °C		1,5 (1,5)	1,8 (1,8)	V				
V _(TO)	T _i = 25 (125) °C		1 (0,9)	1,1 (1)	V				
r _T	T _i = 25 (125) °C		9 (10)	12 (14)	mΩ				
R _{th(j-s)}	per diode		1		K/W				
I _{RRM}	under following conditions		80		Α				
Q _{rr}	I _F = 60 A, V _B = 300 V		7,5		μC				
E _{rr}	V _{GE} = 0 V, T _i = 125 °C		1,7		mJ				
	di _F /dt = 2200 A/µs								
Diode - R	ectifier								
V _F	I _F = 35 A, T _i = 25 °C		1,1		V				
V _(TO)	T _i = 150 °C		0,8		V				
r _T	T _i = 150 °C		11		mΩ				
R _{th(j-s)}	per diode		0,9		K/W				
	ure Sensor	I			1				
R _{ts}	3 %, T _r = 25 (100) °C		1000(1670)		Ω				
Mechanic					1				
w		1	95		g				
Ms	Mounting torque	2		2,5	Nm				

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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